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September 2015

FDMD85100

Dual N-Channel PowerTrench® MOSFET

Q1: 100 V, 48A, 9.9 mΩ Q2: 100 V, 48A, 9.9 mΩ

Features

Q1: N-Channel

■ Max $r_{DS(on)}$ = 9.9 mΩ at V_{GS} = 10 V, I_D = 10.4 A

■ Max $r_{DS(on)}$ = 16.4 mΩ at V_{GS} = 6 V, I_D = 8 A

Q2: N-Channel

■ Max $r_{DS(on)}$ = 9.9 mΩ at V_{GS} = 10 V, I_D = 10.4 A

■ Max $r_{DS(on)}$ = 16.4 mΩ at V_{GS} = 6 V, I_D = 8 A

■ Ideal for flexible layout in primary side of bridge topology

■ Termination is Lead-free and RoHS Compliant

■ 100% UIL tested

■ Kelvin High Side MOSFET drive pin-out capability



General Description

This device includes two 100V N-Channel MOSFETs in a dual Power (5 mm X 6 mm) package. HS source and LS Drain internally connected for half/full bridge, low source inductance package, low $r_{DS(on)}$ /Qg FOM silicon.

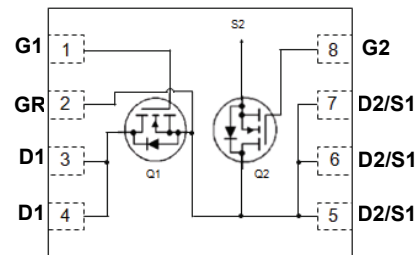
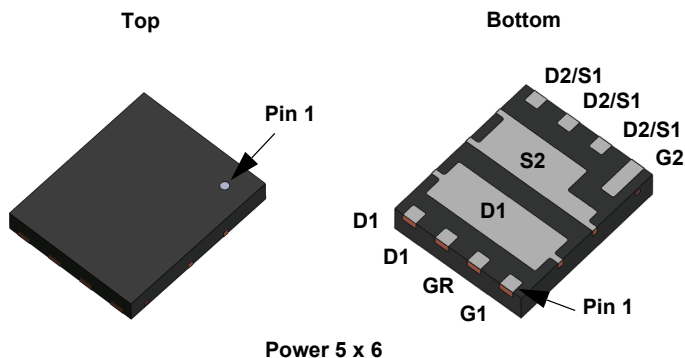
Applications

■ Synchronous Buck : Primary Switch of Half / Full Bridge Bonverter for Telecom

■ Motor Bridge : Primary Switch of Half / Full Bridge Converter for BLDC Motor

■ MV POL : 48V Synchronous Buck Switch

■ Half/Full Bridge Secondary Synchronous Rectification



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Q1	Q2	Units
V_{DS}	Drain to Source Voltage	100	100	V
V_{GS}	Gate to Source Voltage	± 20	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 5)	48	48	A
	-Continuous $T_C = 100^\circ\text{C}$ (Note 5)	30	30	
	Drain Current -Continuous $T_A = 25^\circ\text{C}$	10.4^{1a}	10.4^{1b}	
	-Pulsed (Note 4)	261	261	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	294	294	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	50	50	W
	Power Dissipation $T_A = 25^\circ\text{C}$	2.2^{1a}	2.2^{1b}	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.5	2.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	55^{1a}	55^{1b}	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMD85100	FDMD85100	Power 5 x 6	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	Q1 Q2	100 100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		72 70		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$	Q1 Q2			1 1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$	Q1 Q2			± 100 ± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	Q1 Q2	2.0 2.0	3.1 3.0	4.0 4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		-11 -10		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 10.4\text{ A}$	Q1		7.8	9.9	m Ω
		$V_{GS} = 6\text{ V}$, $I_D = 8\text{ A}$			12.6	16.4	
		$V_{GS} = 10\text{ V}$, $I_D = 10.4\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			14.7	18.7	
		$V_{GS} = 10\text{ V}$, $I_D = 10.4\text{ A}$	Q2		7.8	9.9	
		$V_{GS} = 6\text{ V}$, $I_D = 8\text{ A}$			12.9	16.4	
		$V_{GS} = 10\text{ V}$, $I_D = 10.4\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			14.6	18.6	
g_{FS}	Forward Transconductance	$V_{DD} = 5\text{ V}$, $I_D = 10.4\text{ A}$	Q1 Q2		27 26		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$	Q1 Q2		1590 1485	2230 2080	pF
C_{oss}	Output Capacitance		Q1 Q2		334 337	470 475	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		13 13	23 23	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	1.5 1.3	3.8 3.3	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$, $I_D = 10.4\text{ A}$ $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		14 12.5	25 23	ns
t_r	Rise Time		Q1 Q2		5 5.6	10 11	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		19 18	30 32	ns
t_f	Fall Time		Q1 Q2		4.2 4.4	10 10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	Q1 Q2		22 21	31 29	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 6 V	Q1 Q2		14 13.5	20 19	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = 50\text{ V}$, $I_D = 10.4\text{ A}$	Q1 Q2		7.3 6.8		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		4.3 4.4		nC

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

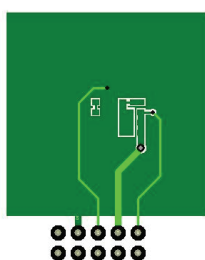
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Drain-Source Diode Characteristics

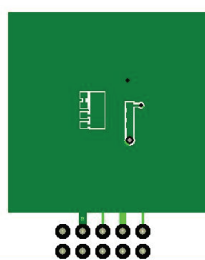
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 10.4\text{ A}$ (Note 2)	Q1 Q2		0.8 0.8	1.3 1.3	V
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2\text{ A}$ (Note 2)	Q1 Q2		0.7 0.7	1.2 1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 10.4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	Q1 Q2		48 47	77 75	ns
Q_{rr}	Reverse Recovery Charge		Q1 Q2		53 51	85 82	nC

NOTES:

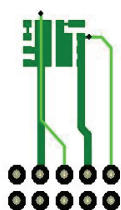
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



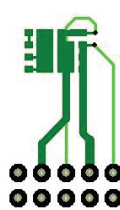
a. 55 °C/W when mounted on
a 1 in² pad of 2 oz copper



b. 55 °C/W when mounted on
a 1 in² pad of 2 oz copper



c. 155 °C/W when mounted on
a minimum pad of 2 oz copper



d. 155 °C/W when mounted on
a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0 %.

3. Q1: E_{AS} of 294 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 14\text{ A}$, $V_{DD} = 90\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 46\text{ A}$.

- Q2: E_{AS} of 294 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 14\text{ A}$, $V_{DD} = 90\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 45\text{ A}$.

4. Pulsed I_d please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

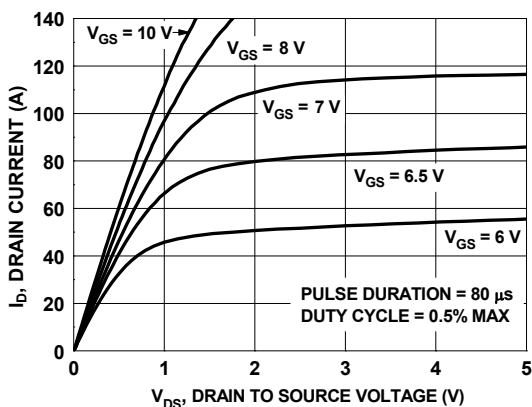


Figure 1. On Region Characteristics

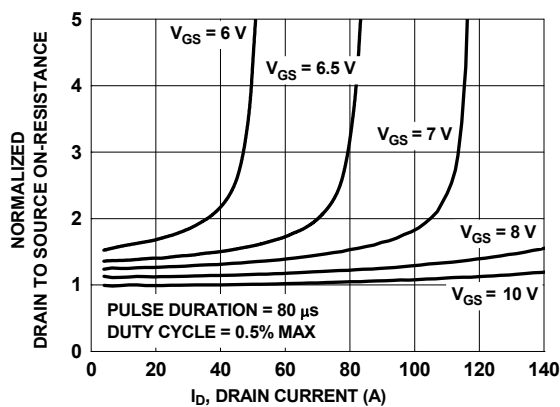


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

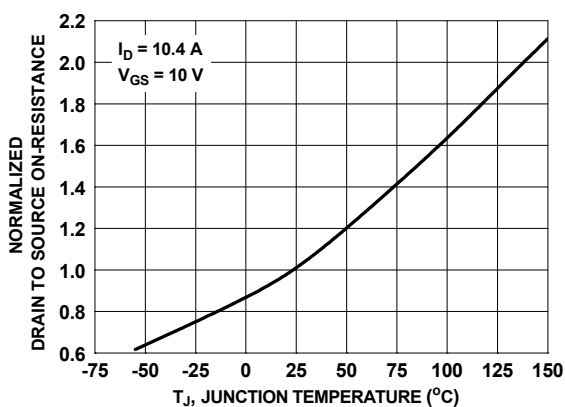


Figure 3. Normalized On Resistance vs. Junction Temperature

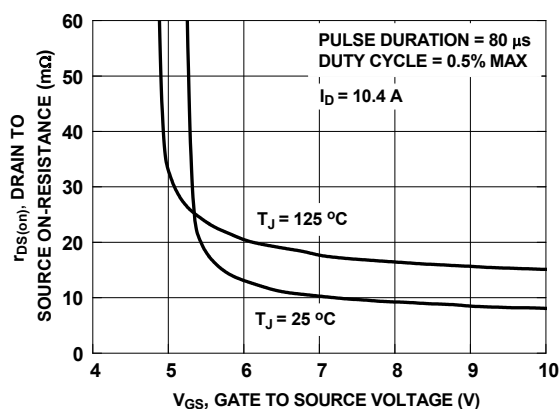


Figure 4. On-Resistance vs. Gate to Source Voltage

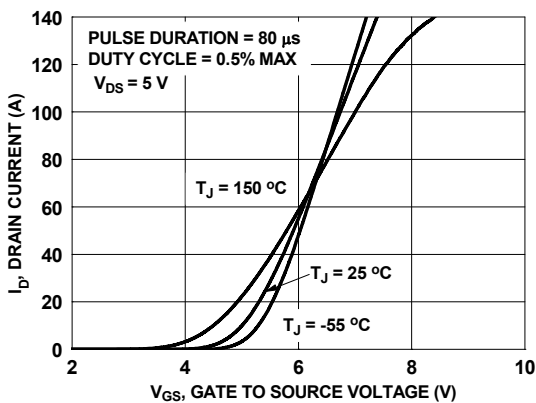


Figure 5. Transfer Characteristics

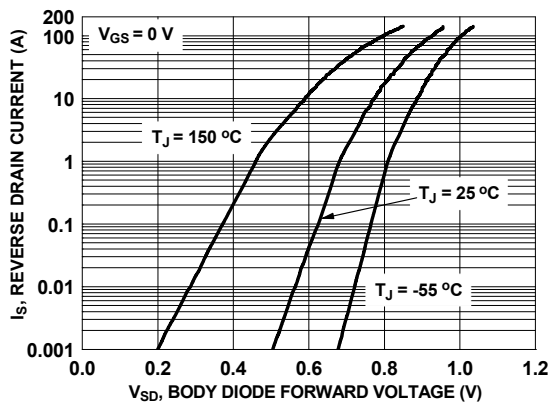


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

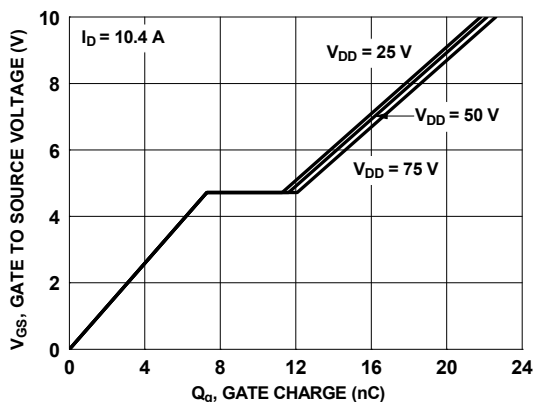


Figure 7. Gate Charge Characteristics

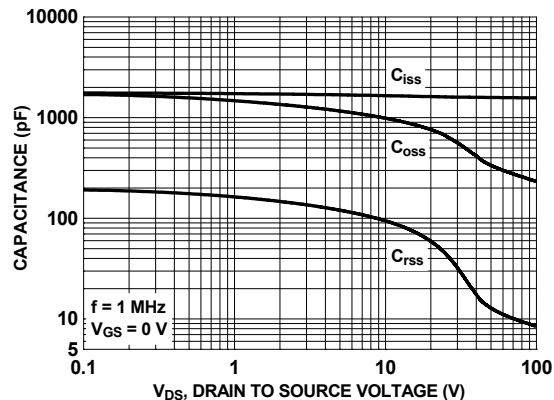


Figure 8. Capacitance vs. Drain to Source Voltage

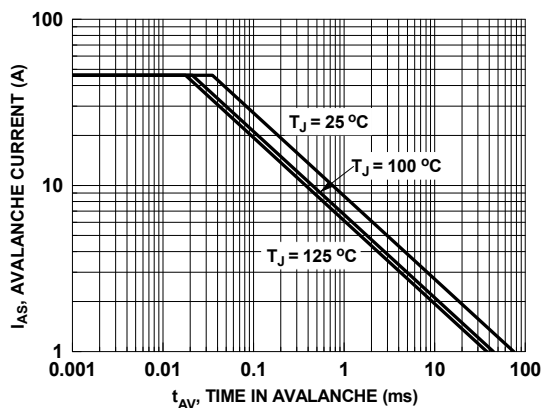


Figure 9. Unclamped Inductive Switching Capability

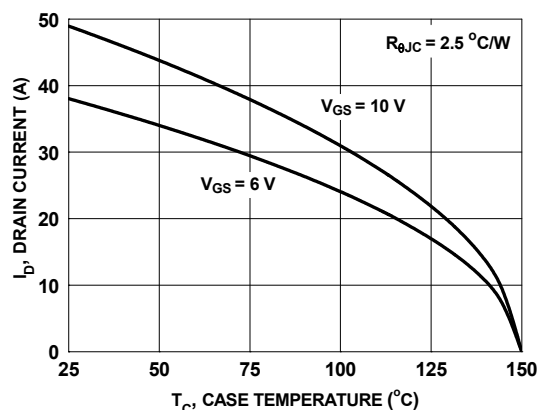


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

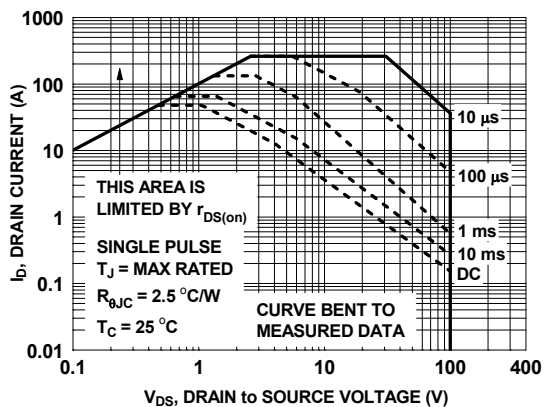


Figure 11. Forward Bias Safe Operating Area

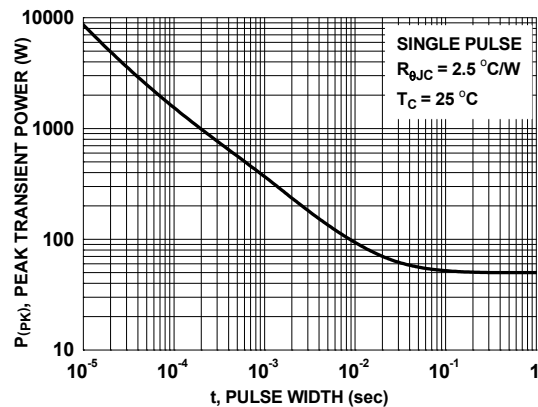


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

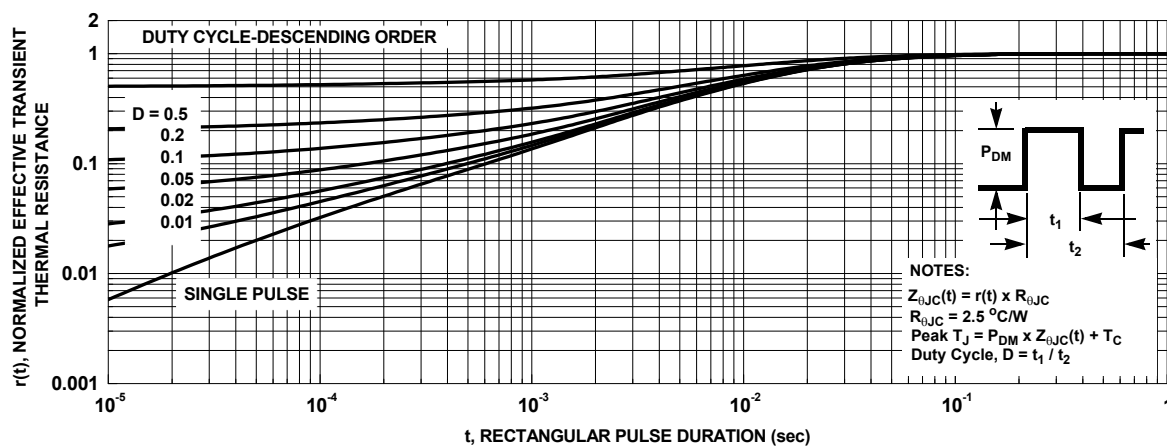


Figure 13. Junction-to-Case Transient Thermal Response Curve

Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

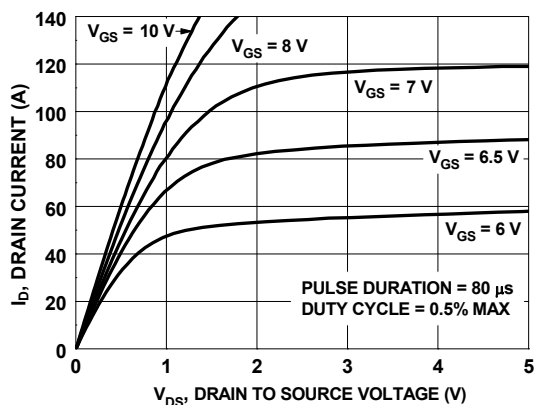


Figure 14. On-Region Characteristics

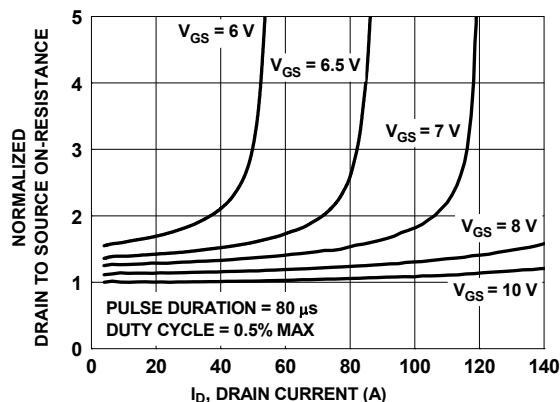


Figure 15. Normalized on-Resistance vs. Drain Current and Gate Voltage

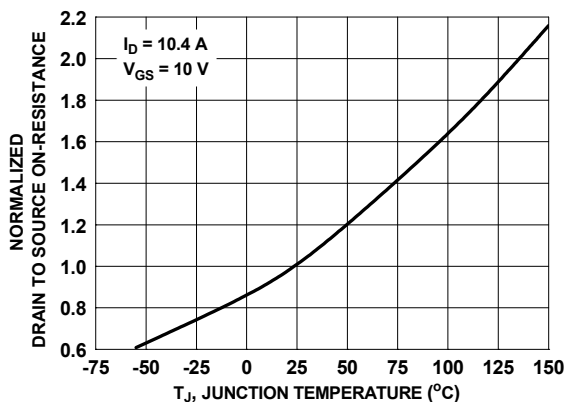


Figure 16. Normalized On-Resistance vs. Junction Temperature

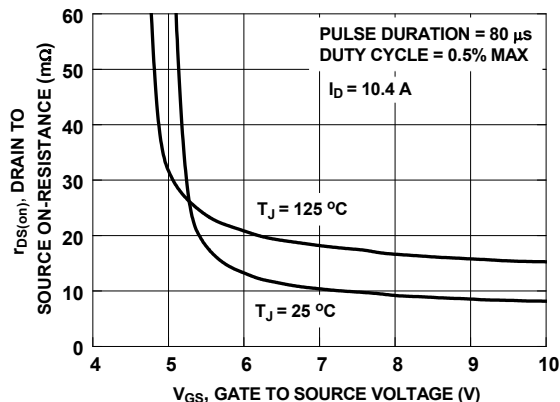


Figure 17. On-Resistance vs. Gate to Source Voltage

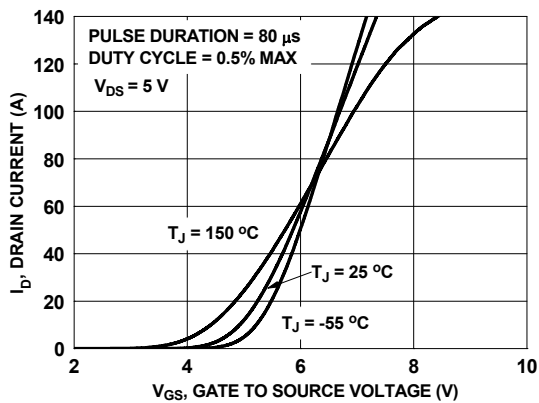


Figure 18. Transfer Characteristics

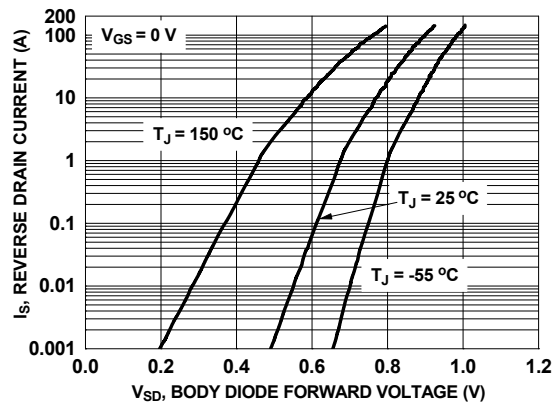


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

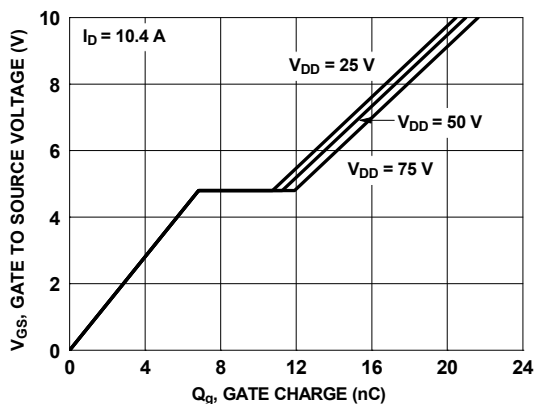


Figure 20. Gate Charge Characteristics

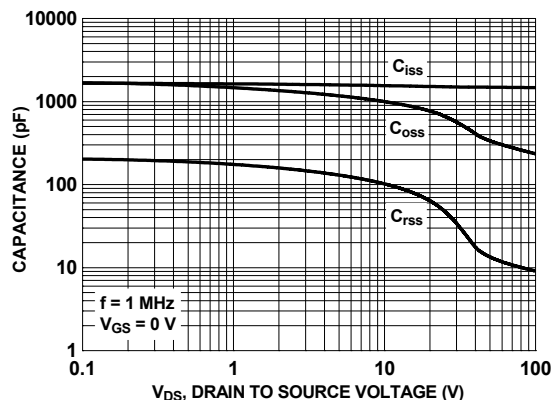


Figure 21. Capacitance vs. Drain to Source Voltage

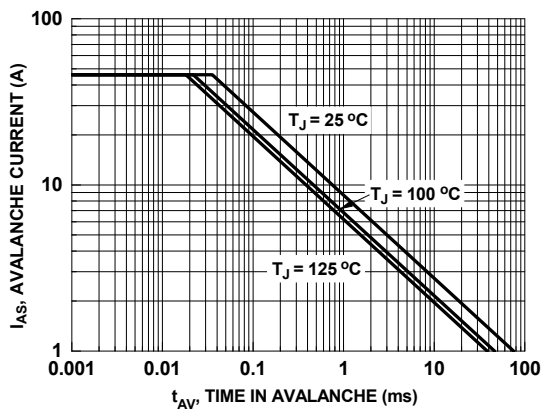


Figure 22. Unclamped Inductive Switching Capability

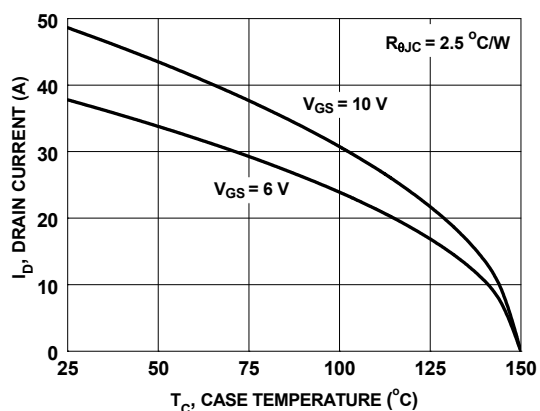


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

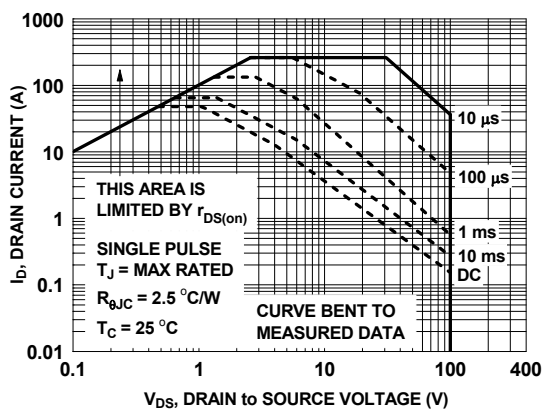


Figure 24. Forward Bias Safe Operating Area

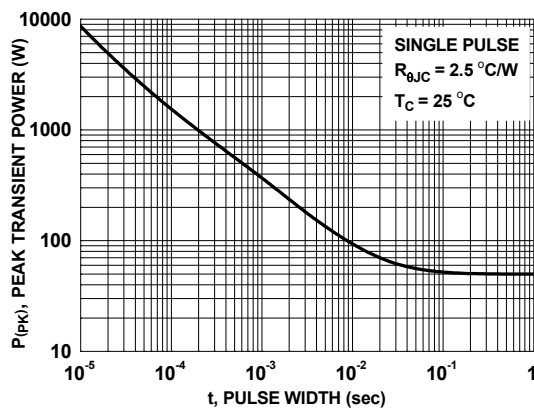


Figure 25. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

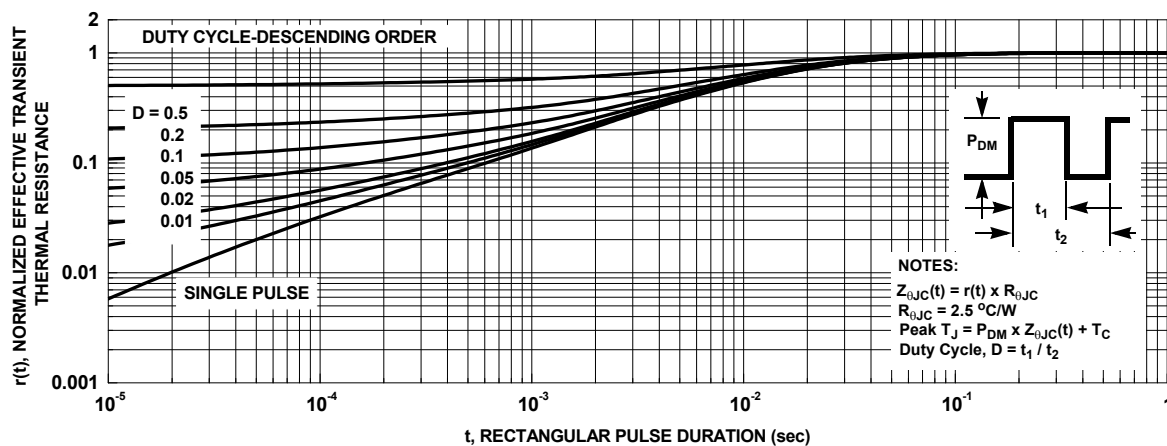


Figure 26. Junction-to-Case Transient Thermal Response Curve

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